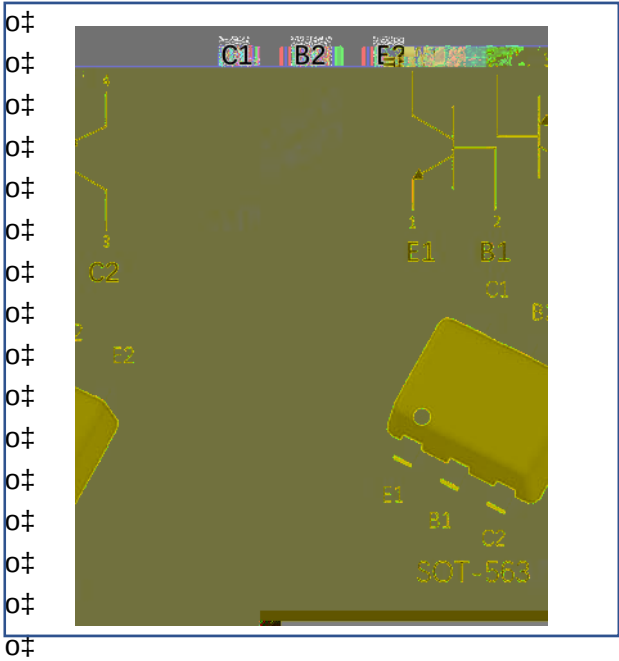




Dual NPN+PNP Small Signal Transistor



Features

- z 0RLVWXUH VHQVLWLYLW\ OHYHO
- z +DORJHQ IUHH DQG 5R+6 FRPSOL
- z 6XUIDFH PRXQW SDFNDJH LGHDOO
- PDWLF ,QVHUWLRQ

Application

- z 6LJQDO DPSOLILFDWLRQ
- z 6ZLWFKLQJ FLUFXLW

Mechanical data

- z Package SOT-563
- z Terminals Tin plated leads , solderable per J-STD-0 0 2 and JESD22-B1 0 2

0±

TR1-NPN

Item	Symbol	Unit	Conditions	Value
Device marking code				Z7
Collector-base voltage	V_{CBO}	V	$I_C = 100\mu A, 0$	15
Collector-emitter voltage	V_{CEO}	V	$I_C = 1mA, \beta = 0$	12
Emitter-base voltage	V_{EBO}	V	$I_E = 100\mu A, 0$	6
Collector current	I_C	mA		500
Power dissipation	P_D	mW		150
J unction temperature	T_J	°C		-55 to +150

Unless otherwise specified)



EMZ7

TR2-PNP

Item	Symbol	Unit	Conditions	Value
Collector-base voltage	V_{CB0}	V	$I_C = -100\mu A, 0$	-15
Collector-emitter voltage	V_{CE0}	V	$I_C = -1mA, I_B = 0$	-12
Emitter-Base voltage	V_{EB0}	V	$I_E = -100\mu A, 0$	-6
Collector current	I_C	mA		-500
Power dissipation	P_D	mW		150
J unction temperature	T_J			-55 to +150
Storage temperature	T_{TG}			-55 to +150

TR1-NPN

Item	Symbol	Unit	Conditions	Min	Typ	Max
Collector-base breakdown voltage	$V_{(BR)CBO}$	V	$I_C = 100\mu A, 0$	15		
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	V	$I_C = 1mA, I_B = 0$	12		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	V	$I_E = 100\mu A, 0$	6		

Collector-base cut-off current I



EMZ7

RoHS
COMPLIANT

TR2-PNP

Item	Symbol	Unit	Conditions	Min	Typ	Max
Collector-base breakdown voltage	$V_{(BR)CBO}$					



EMZ7

RoHS

COMPLIANT





Fig 7 P_D-T_a Curve

TR2-PNP

Fig 1 Static Characteristics

Fig 2 DC Current Gain Characteristics

oratio Fig 3 Collector-Emitte f t



EMZ7

RoHS
COMPLIANT



EMZ7

RoHS
COMPLIANT

0‡
0‡
0‡
0‡

Preferred P/M

Ł M ģ - / n

